

N-channel 650 V, 0.049 Ω typ., 49 A MDmesh™ M2 Power MOSFET in a TO247-4 package

Datasheet - production data

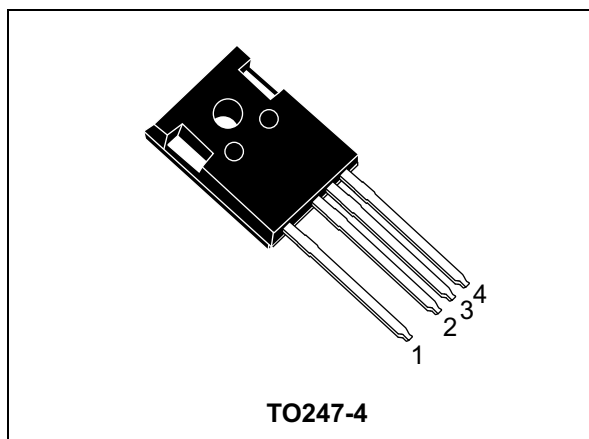
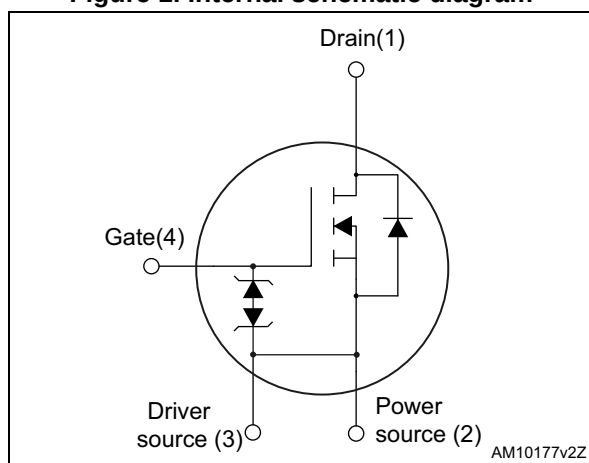


Figure 1. Internal schematic diagram



Features

Order code	V_{DS}	$R_{DS(on)}$ max	I_D
STW56N65M2-4	650 V	0.062 Ω	49 A

- Excellent switching performance thanks to the extra driving source pin
- Extremely low gate charge
- Excellent output capacitance (C_{OSS}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using MDmesh™ M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

Table 1. Device summary

Order code	Marking	Package	Packaging
STW56N65M2-4	56N65M2	TO247-4	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate- source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	49	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	31	A
$I_{DM}^{(1)}$	Drain current (pulsed)	196	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	358	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature	- 55 to 150	$^{\circ}\text{C}$
T_j	Max. operating junction temperature	150	$^{\circ}\text{C}$

1. Pulse width limited by safe operating area

2. $I_{SD} \leq 49\text{ A}$, $di/dt = 400\text{ A}/\mu\text{s}$, $V_{DS(\text{peak})} < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$

3. $V_{DS} \leq 520\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-amb}$	Thermal resistance junction-ambient max	50	$^{\circ}\text{C}/\text{W}$
$R_{thj-case}$	Thermal resistance junction-case max	0.35	$^{\circ}\text{C}/\text{W}$

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Max current during repetitive or single pulse avalanche (pulse width limited by T_{JMAX})	3.5	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	1300	mJ

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	650			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 650\text{ V}$ $V_{DS} = 650\text{ V}$, $T_C = 125\text{ °C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 25\text{ V}$			± 10	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 24.5\text{ A}$		0.049	0.062	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	3900	-	pF
C_{oss}	Output capacitance		-	160	-	pF
C_{rss}	Reverse transfer capacitance		-	2.8	-	pF
$C_{o(er)}^{(1)}$	Equivalent Output Capacitance	$V_{GS} = 0$, $V_{DS} = 0\text{ to }520\text{ V}$	-	838	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	4.6	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}$, $I_D = 49\text{ A}$, $V_{GS} = 10\text{ V}$, (see Figure 15)	-	93	-	nC
Q_{gs}	Gate-source charge		-	16	-	nC
Q_{gd}	Gate-drain charge		-	40	-	nC

1. C_{oss} eq. is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325\text{ V}$, $I_D = 24.5\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 16 and Figure 19)	-	19	-	ns
t_r	Rise time		-	27.5	-	ns
$t_{d(off)}$	Turn-off delay time		-	146	-	ns
t_f	Fall time		-	13	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		49	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		196	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 49\text{ A}$, $V_{GS} = 0$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 49\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see Figure 16)	-	554		ns
Q_{rr}	Reverse recovery charge		-	13.5		μC
I_{RRM}	Reverse recovery current		-	49.5		A
t_{rr}	Reverse recovery time	$I_{SD} = 49\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 19)	-	688		ns
Q_{rr}	Reverse recovery charge		-	18		μC
I_{RRM}	Reverse recovery current		-	52		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

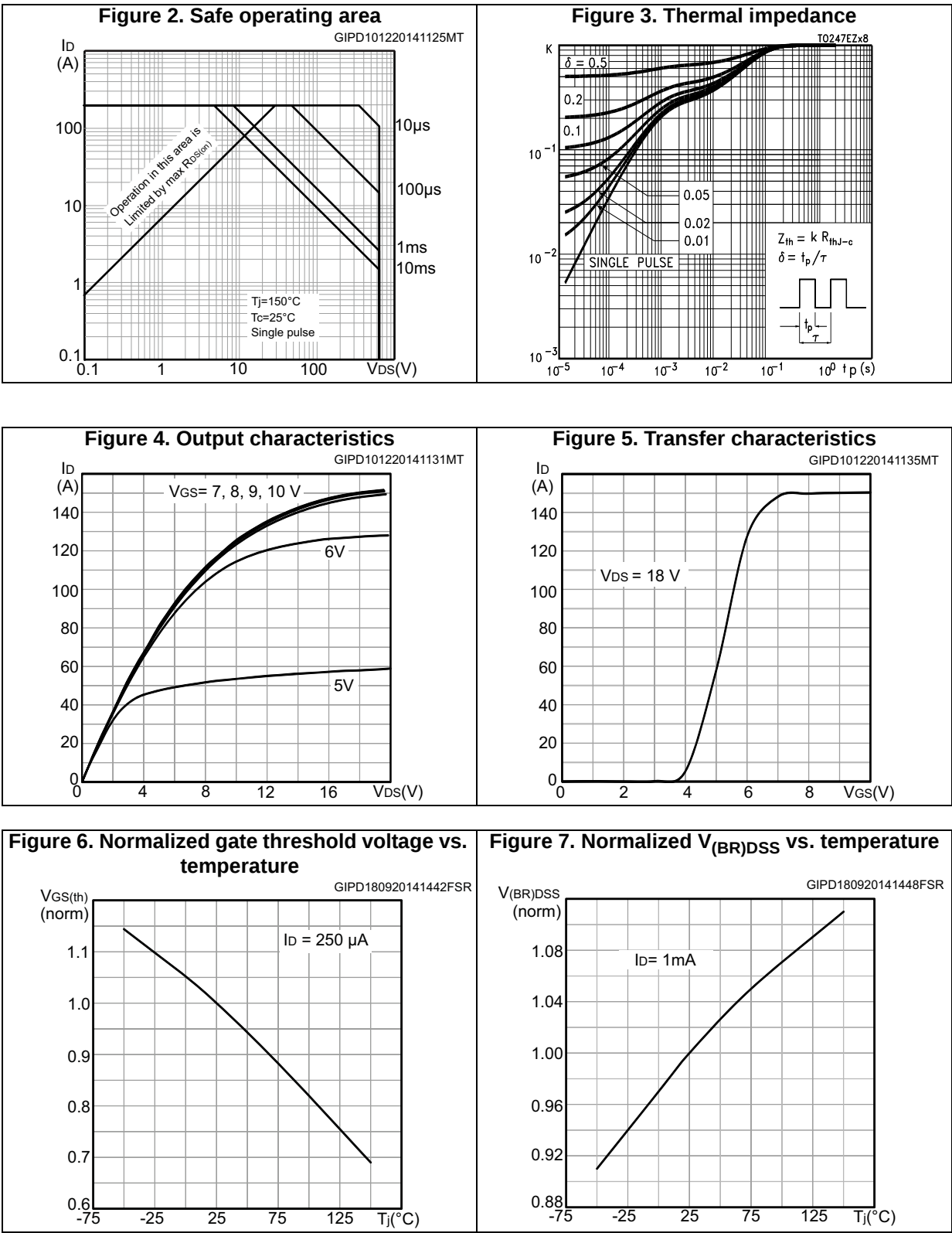


Figure 8. Static drain-source on-resistance

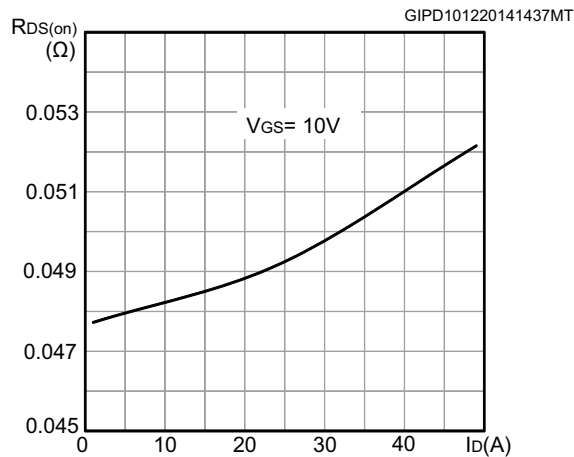


Figure 9. Normalized on-resistance vs. temperature

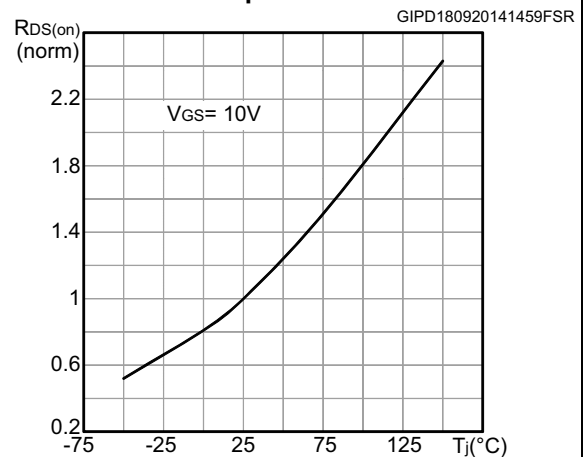


Figure 10. Gate charge vs. gate-source voltage

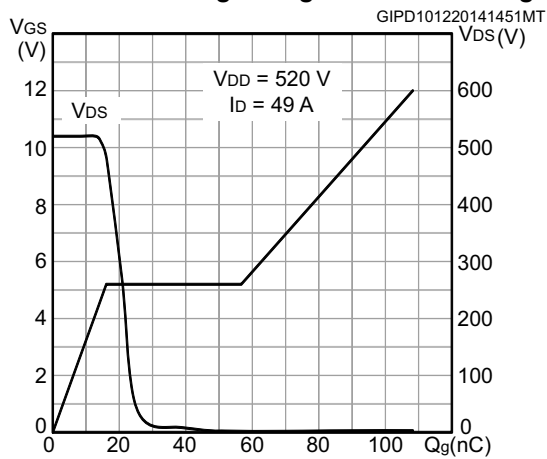


Figure 11. Capacitance variations

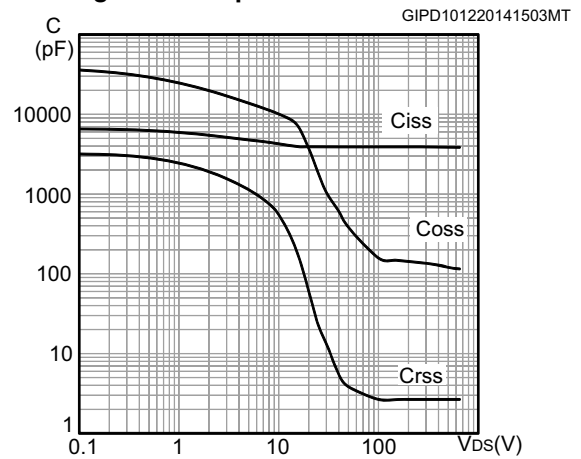


Figure 12. Output capacitance stored energy

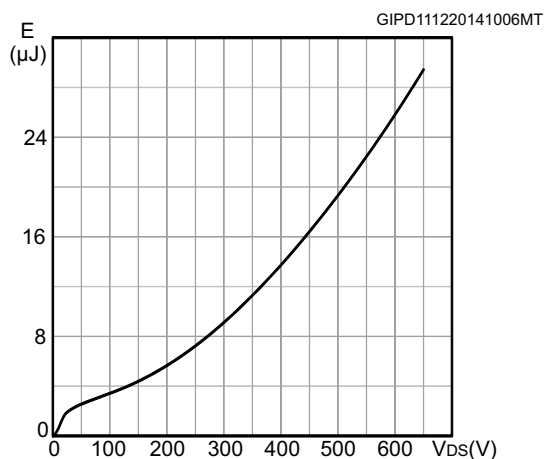
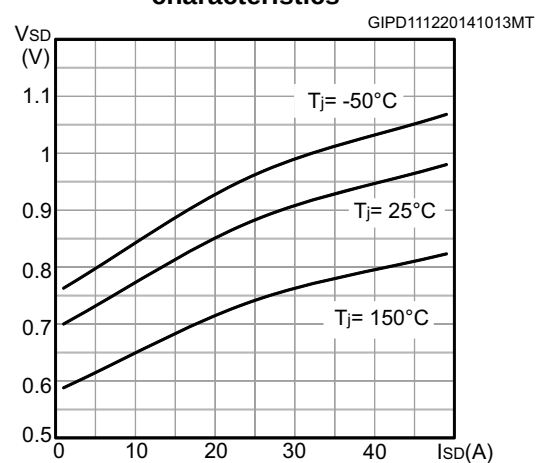
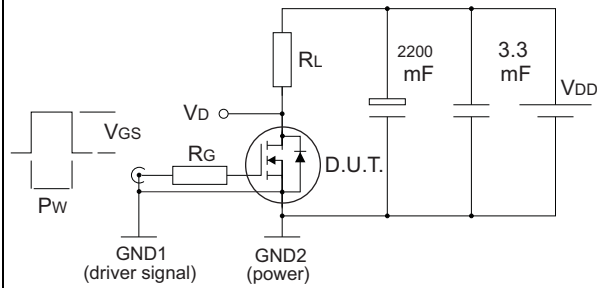


Figure 13. Source-drain diode forward characteristics



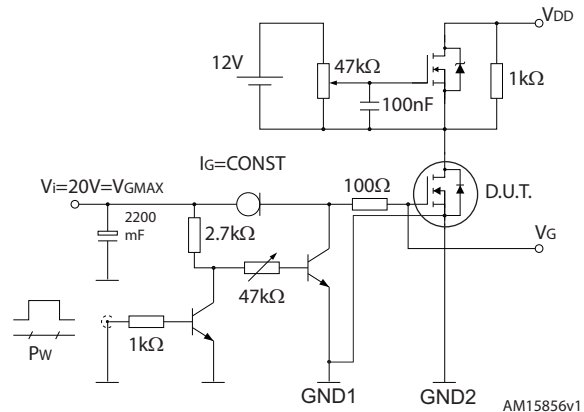
3 Test circuits

Figure 14. Switching times test circuit for resistive load



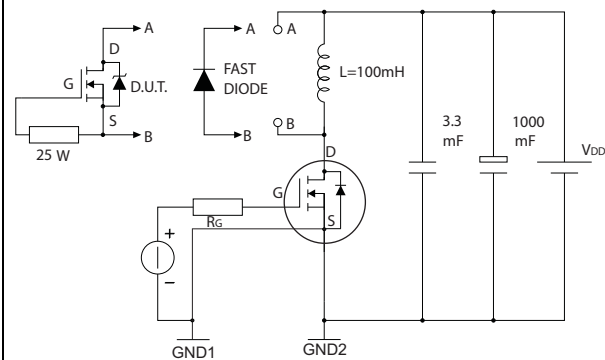
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Figure 15. Gate charge test circuit



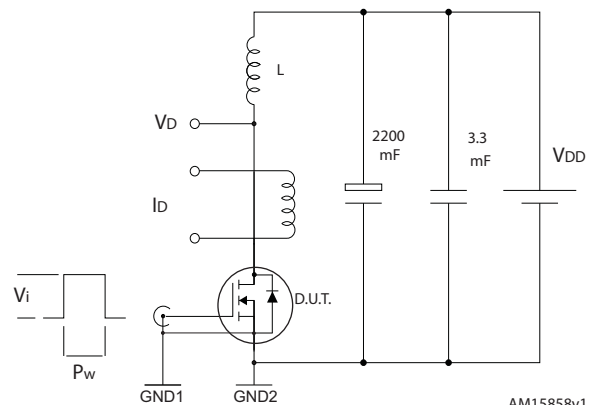
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Figure 16. Test circuit for inductive load switching and diode recovery times



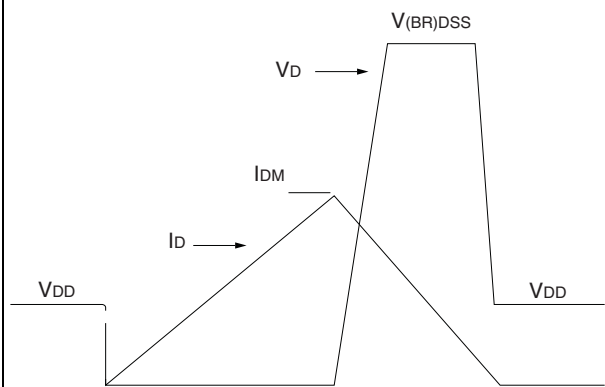
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Figure 17. Unclamped inductive load test circuit



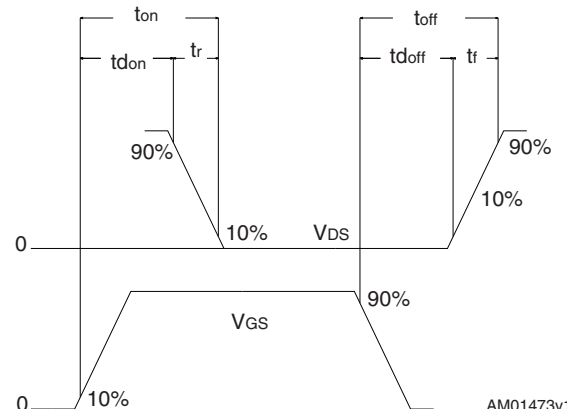
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Figure 18. Unclamped inductive waveform



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Figure 19. Switching time waveform



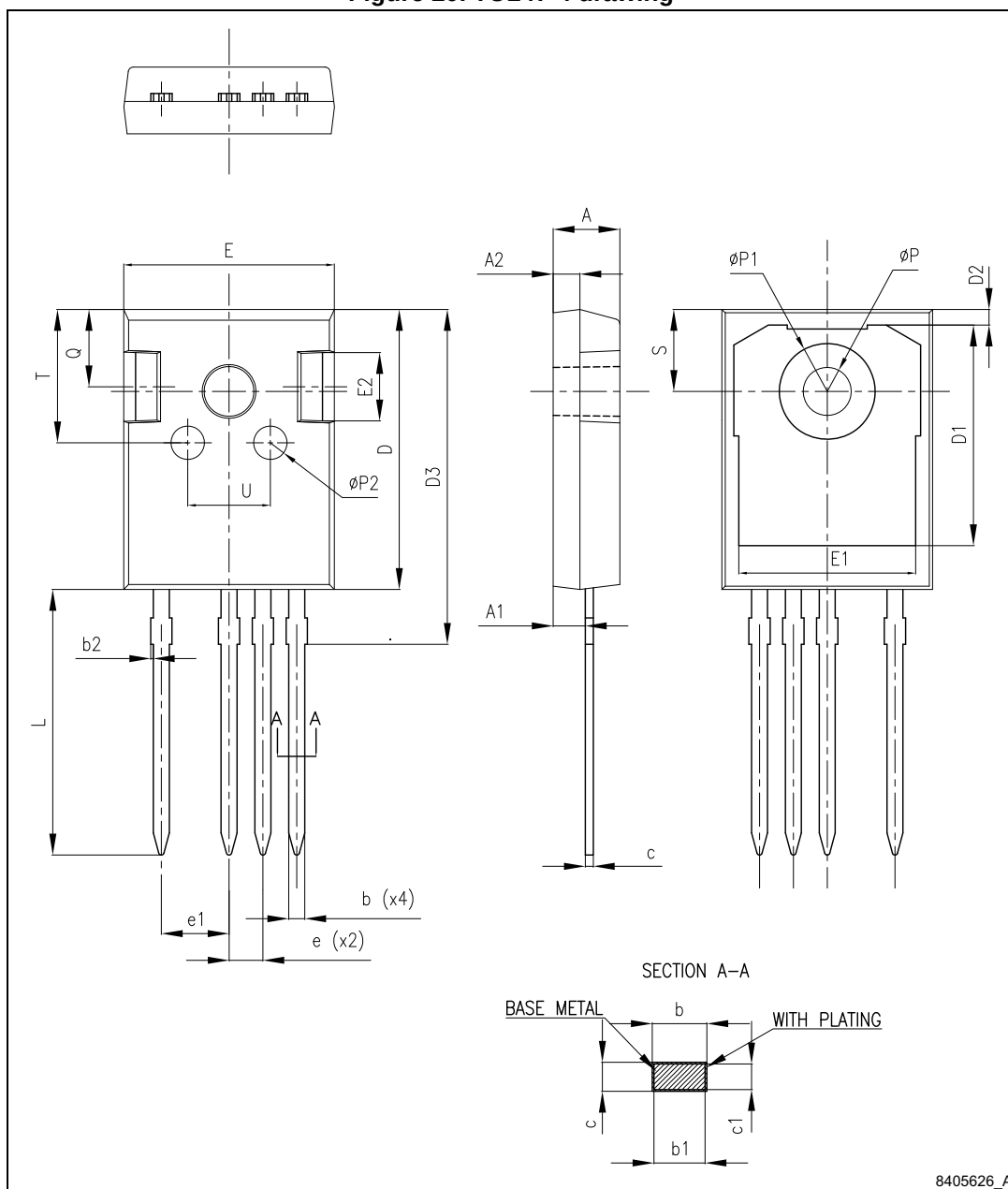
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4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 TO247-4, STW56N65M2-4

Figure 20. TO247-4 drawing



8405626_A

Table 9. TO247-4 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16		1.29
b1	1.15	1.20	1.25
b2	0		0.20
c	0.59		0.66
c1	0.58	0.60	0.62
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.20	1.35
D3	24.97	25.12	25.27
E	15.70	15.80	15.90
E1	13.10	13.30	13.50
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	2.44	2.54	2.64
e1	4.98	5.08	5.18
L	19.80	19.92	20.10
P	3.50	3.60	3.70
P1			7.40
P2	2.40	2.50	2.60
Q	5.60		6.00
S		6.15	
T	9.80		10.20
U	6.00		6.40

5 Revision history

Table 10. Document revision history

Date	Revision	Changes
15-Dec-2014	1	Initial release.

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